

L Number	Hits	Search Text	DB	Time stamp
-	1395	438/240	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 17:06
-	591	438/279	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 10:31
-	1513	438/239	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:55
-	1779	438/238	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 11:19
-	550	438/201	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 11:29
-	618	438/210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 11:40
-	362	438/211	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 11:49
-	3841	257/296	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 15:50
-	850	257/300	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 13:46
-	5090	438/396	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 18:20
-	148	438/240 and ((silicon adj nitride) with CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:04
-	17	438/240 and ((silicon adj nitride) with CVD) and @pd<19991224	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:00
-	43	438/\$.ccls. and ((silicon adj nitride) with (interlayer adj insulating) with (diffused or diffusion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:02
-	13	438/\$.ccls. and ((silicon adj nitride) with (interlayer adj insulating) with (diffused or diffusion)) and @pd<19991224	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 11:07

-	317	438/\$.ccls. and ((silicon adj nitride) with (gas or hydrogen) with substrate) and @pd<19991224	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:55
-	15	438/\$.ccls. and ((silicon adj nitride) with ((gas or hydrogen) with (diffused or diffusion) with substrate)) and @pd<19991224	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:57
-	15	438/\$.ccls. and ((silicon adj nitride) with (gas or hydrogen) with (diffused or diffusion) with substrate) and @pd<19991224	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 11:42
-	14	annealing same (planarize with interlayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 17:55
-	29	(fluorine adj base) with resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 12:20
-	205	(fluorine adj based) with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 12:23
-	132	(fluorine adj based) with resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 12:24
-	41	438/238 and (annealing with hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 18:17
-	4641	257/296	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 17:29
-	1062	257/300	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 07:35
-	3256	257/306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 07:35
-	6	annealing same gas same (interfacial near level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 17:57
-	342	annealing same atmosphere same (water near vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 07:31
-	585	257/307	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 07:40

-	821	257/308	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 07:51
-	1196	257/309	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 08:01
-	756	438/210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 08:08
-	2178	438/238	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 08:26
-	1910	438/239	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 08:40
-	1877	438/240	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 08:53
-	3834	438/253	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 09:21
-	522	438/387	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 09:45
-	574	438/399	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 09:56
-	1370	438/398	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 09:57